

Boca Semiconductor Corp.

BSC

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MAXIMUM RATINGS

Rating	Symbol	2N3250 2N3251	2N3251A	Unit
Collector-Emitter Voltage	V_{CE0}	-40	-60	Vdc
Collector-Base Voltage	V_{CB0}	-50	-60	Vdc
Emitter-Base Voltage	V_{EB0}	-5.0		Vdc
Collector Current	I_C	-200		mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	0.36 2.06		Watt mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.2 6.9		Watts mW/ $^\circ\text{C}$
Operating and Storage Temperature Temperature Range	T_J, T_{stg}	-65 to +200		$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	486	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	146	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage(1) ($I_C = -10$ mAdc)	$V_{(BR)CEO}$	-40 -60	—	Vdc
Collector-Base Breakdown Voltage ($I_C = -10$ μAdc)	$V_{(BR)CBO}$	-50 -60	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = -10$ μAdc)	$V_{(BR)EBO}$	-5.0	—	Vdc
Collector Cutoff Current ($V_{CE} = -40$ Vdc, $V_{EB} = -3.0$ Vdc)	I_{CEX}	—	-20	nA
Base Cutoff Current ($V_{CE} = -40$ Vdc, $V_{EB} = -3.0$ Vdc)	I_{BL}	—	-50	nAdc

ON CHARACTERISTICS

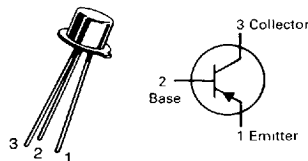
DC Forward Current Transfer Ratio ($I_C = -0.1$ mAdc, $V_{CE} = -10$ Vdc)	h_{FE}	40 80	— —	—
($I_C = -1.0$ mAdc, $V_{CE} = -1.0$ Vdc)		45 90	— —	
($I_C = -10$ mAdc, $V_{CE} = -1.0$ Vdc)(1)		50 100	150 300	
($I_C = -50$ mAdc, $V_{CE} = -1.0$ Vdc)(1)		15 30	— —	
Collector-Emitter Saturation Voltage (1) ($I_C = -10$ mAdc, $I_B = -1.0$ mAdc) ($I_C = -50$ mAdc, $I_B = -5.0$ mAdc)	$V_{CE(sat)}$	— —	-0.25 -0.5	Vdc
Base-Emitter Saturation Voltage (1) ($I_C = -10$ mAdc, $I_B = -1.0$ mAdc) ($I_C = -50$ mAdc, $I_B = -5.0$ mAdc)	$V_{BE(sat)}$	-0.6 —	-0.9 -1.2	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product ($I_C = -10$ mAdc, $V_{CE} = -20$ Vdc, $f = 100$ MHz)	f_T	250 300	— —	MHz
Output Capacitance ($V_{CB} = -10$ Vdc, $I_E = 0$, $f = 1.0$ MHz)	C_{obo}	—	6.0	pF
Input Capacitance ($V_{EB} = -1.0$ Vdc, $I_C = 0$, $f = 1.0$ MHz)	C_{ibo}	—	8.0	pF

2N3250 2N3251A★

CASE 22-03, STYLE 1
TO-18 (TO-206AA)



GENERAL PURPOSE TRANSISTORS

PNP SILICON

★2N3251A is a Motorola
designated preferred device.

2N3250 2N3251,A

ELECTRICAL CHARACTERISTICS (continued) ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
Input Impedance ($I_C = -1.0\text{ mA}$, $V_{CE} = -10\text{ V}$, $f = 1.0\text{ kHz}$)	2N3250 2N3251, 2N3251A	h_{ie}	1.0 2.0	6.0 12	kohms
Voltage Feedback Ratio ($I_C = -1.0\text{ mA}$, $V_{CE} = -10\text{ V}$, $f = 1.0\text{ kHz}$)	2N3250 2N3251, 2N3251A	h_{re}	—	10 20	$\times 10^{-4}$
Small-Signal Current Gain ($I_C = -1.0\text{ mA}$, $V_{CE} = -10\text{ V}$, $f = 1.0\text{ kHz}$)	2N3250 2N3251, 2N3251A	h_{fe}	50 100	200 400	—
Output Admittance ($I_C = -1.0\text{ mA}$, $V_{CE} = -10\text{ V}$, $f = 1.0\text{ kHz}$)	2N3250 2N3251, 2N3251A	h_{oe}	4.0 10	40 60	μmhos
Collector Base Time Constant ($I_C = -10\text{ mA}$, $V_{CE} = -20\text{ V}$, $f = 31.8\text{ MHz}$)		$r_b' C_C$	—	250	ps
Noise Figure ($I_C = -100\text{ }\mu\text{A}$, $V_{CE} = -5.0\text{ V}$, $R_S = 1.0\text{ k}\Omega$, $f = 100\text{ Hz}$)		NF	—	6.0	dB

SWITCHING CHARACTERISTICS

Characteristic		Symbol	Max	Unit
Delay Time	($V_{CC} = -3.0\text{ Vdc}$, $V_{BE} = +0.5\text{ Vdc}$ $I_C = -10\text{ mAdc}$, $I_{B1} = -1.0\text{ mA}$)	t_d	35	ns
Rise Time		t_r	35	ns
Storage Time	$I_C = -10\text{ mAdc}$, $I_{B1} = I_{B2} = -1.0\text{ mAdc}$ ($V_{CC} = -3.0\text{ V}$)	t_s	175 200	ns
Fall Time			t_f	50

(1) Pulse Test: $PW = 300\text{ }\mu\text{s}$, Duty Cycle = 2.0%.

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SWITCHING TIME CHARACTERISTICS

FIGURE 1 — DELAY AND RISE TIME

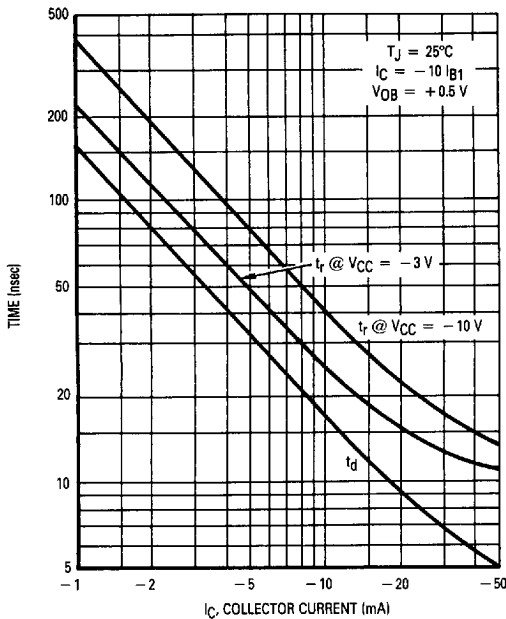
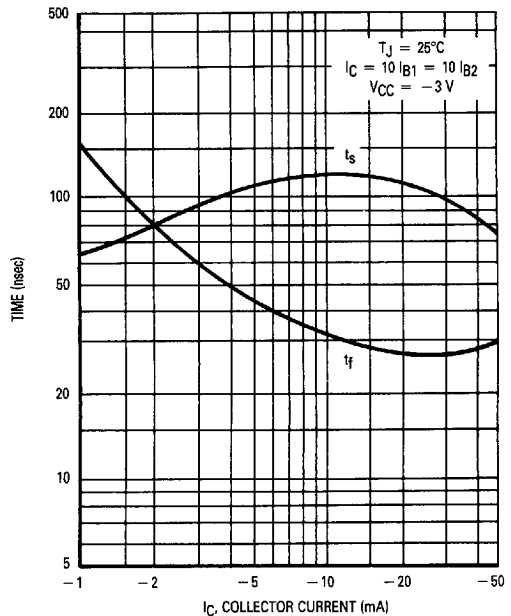


FIGURE 2 — STORAGE AND FALL TIME



AUDIO SMALL-SIGNAL CHARACTERISTICS
NOISE FIGURE VARIATIONS
 ($V_{CE} = 6.0 \text{ V}$, $T_A = 25^\circ\text{C}$)

FIGURE 3 — FREQUENCY

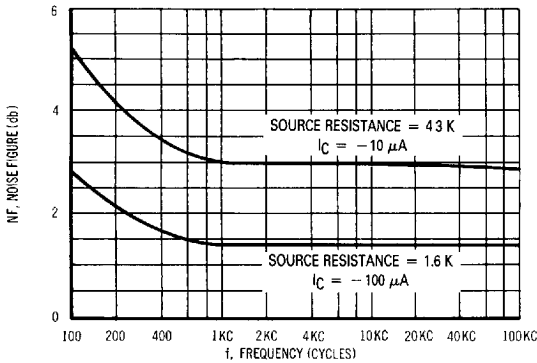
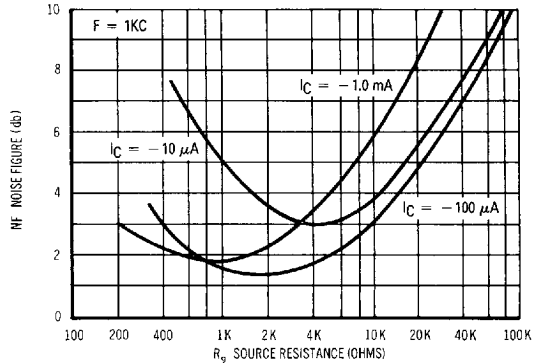


FIGURE 4 — SOURCE RESISTANCE



h PARAMETERS

$V_{CE} = 10 \text{ V}$, $f = 1.0 \text{ kc}$, $T_A = 25^\circ\text{C}$

FIGURE 5 — CURRENT GAIN

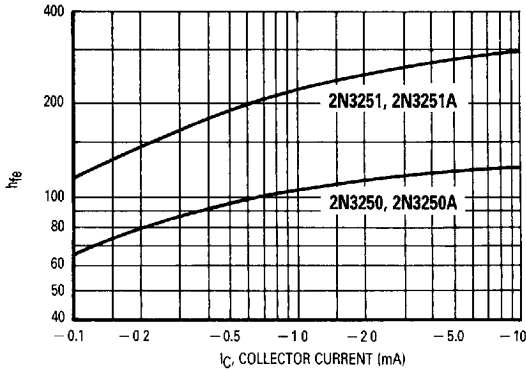


FIGURE 6 — OUTPUT ADMITTANCE

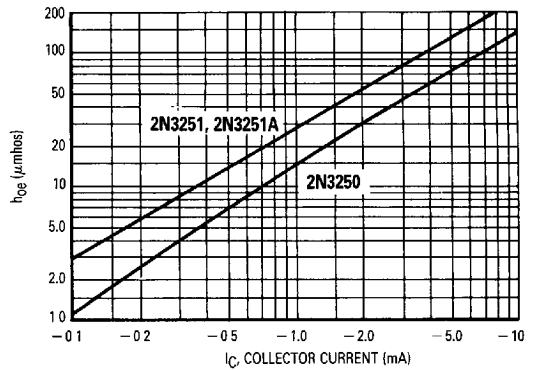


FIGURE 7 — VOLTAGE FEEDBACK RATIO

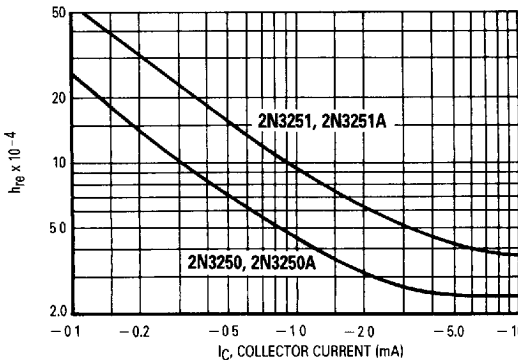
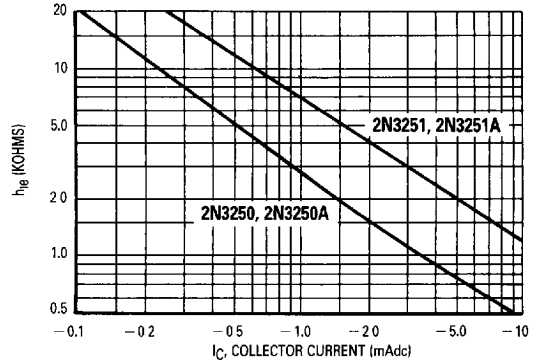


FIGURE 8 — INPUT IMPEDANCE



2N3250 2N3251,A

FIGURE 9 — NORMALIZED CURRENT GAIN CHARACTERISTICS

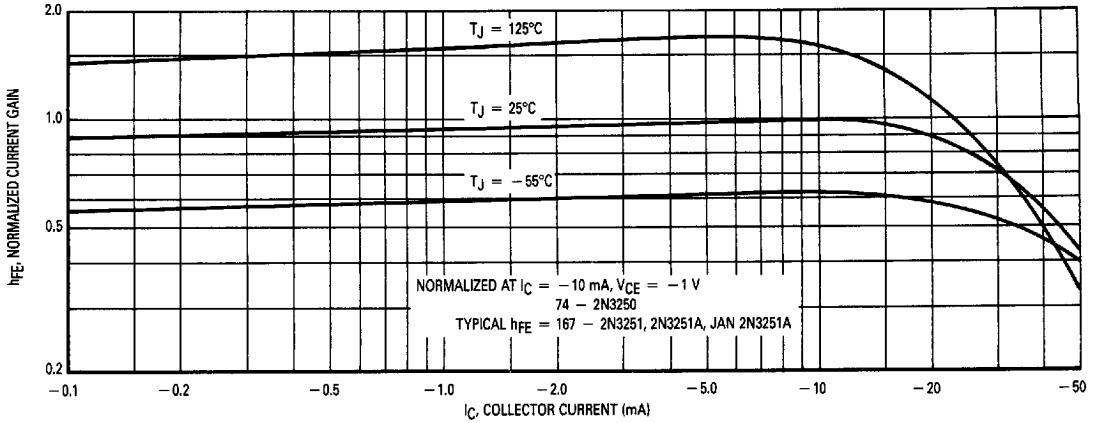


FIGURE 10 — COLLECTOR SATURATION REGION

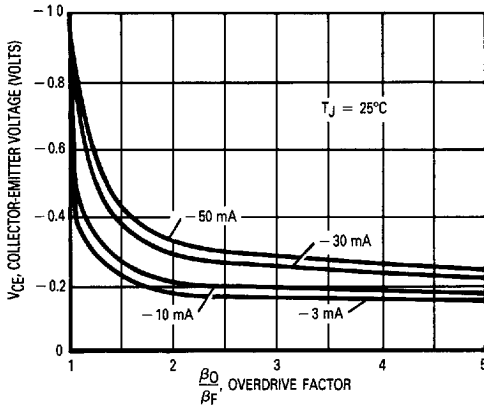
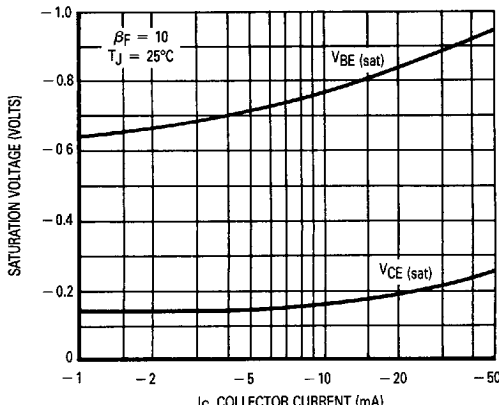


FIGURE 11 — SATURATION VOLTAGES



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This graph shows the effect of base current on collector current β_O is the current gain of the transistor at 1 volt, and β_F (forced gain) is the ratio of I_C/I_{BF} in a circuit. EXAMPLE: For type 2N3251, estimate a base current (I_{BF}) to insure saturation at a temperature of 25°C and a collector current of 10 mA.

Observe that at $I_C = 10\text{ mA}$ an overdrive factor of at least 2.5 is required to drive the transistor well into the saturation region. From Figure 1, it is seen that $h_{FE} @ 1\text{ volt}$ is typically 167 (guaranteed limits from the Table of Characteristics can be used for "worst case" design).

$$\frac{\beta_O}{\beta_F} = \frac{h_{FE} @ 1\text{ Volt}}{I_C/I_{BF}} \quad 2.5 = \frac{167}{10\text{ mA}/I_{BF}} \quad I_{BF} \approx -6.68\text{ mA}$$

FIGURE 12 — TEMPERATURE COEFFICIENTS

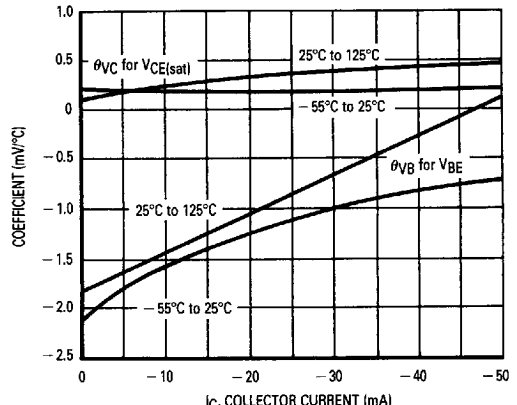


FIGURE 13 — f_T AND $r_b'C_c$ versus I_C

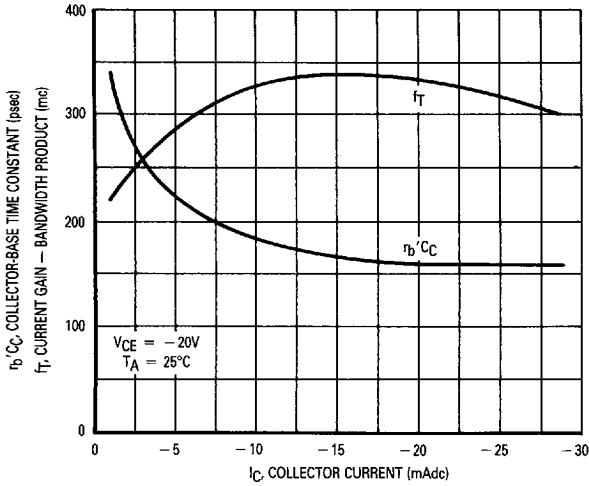
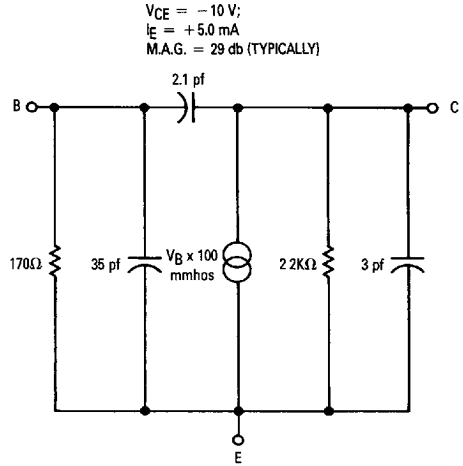


FIGURE 14 — 30 MC EQUIVALENT CIRCUIT



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FIGURE 15 — JUNCTION CAPACITANCE

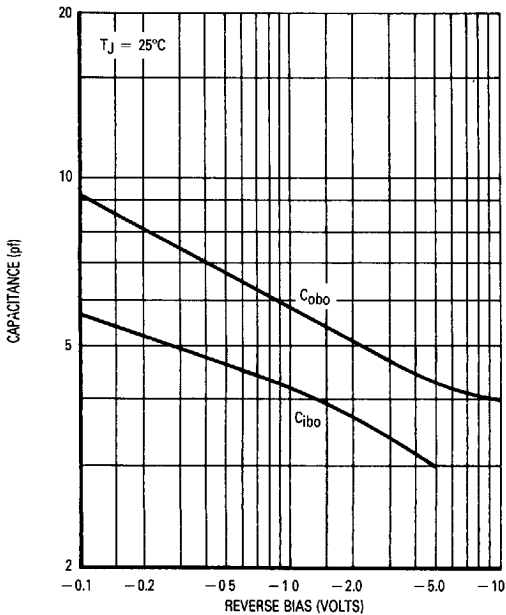


FIGURE 16 — CHARGE DATA

